

REMARKS**1. Allowable subject matter:**

5 *Claim 5, 12 objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.*

10 The Applicants note the Examiner's comments remarks regarding allowable subject matter upon first consideration of the instant application.

2. Claim rejections – 35 USC § 102:

15 *Claims 1-4 and 6-11 are rejected under 35 USC 102 (b) as being anticipated by Goo (U.S. Patent 5,677,215).*

Response:

20 Regarding claims 1-4, during the following discussion, the Applicants will endeavor to clearly state the salient differences between the cited prior art, Goo (U.S. Patent 5,677,215) – herein after referred to as Goo, and the claimed invention embodiment recited by claims 1-4.

25 The Applicants point out that while Goo is primarily directed at a more efficient manufacturing method for a semiconductor memory device, the present invention is directed at increasing the density of such memory devices by providing a single instance of a ROM cell disposed on a semiconductor substrate with multiple drain signals, instead of the single drain signal of the prior art, thereby enabling the ROM cell of the present invention to store more than one data bit.

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 Claim 1 of the instant invention can be understood from Fig.2 and Fig.3 although claim 1 is not limited to the embodiment in these figures. Figs.2 and 3 clearly show a

drain doped region (210), this recited as "a first doped region being of a second conductive type installed on the silicon substrate", and further heavily doped regions (212a & 212b) of a different conductive type formed in the drain doped region (210), these being recited as "a plurality of first heavily doped regions being of a first conductive type installed in the first doped region". Whereas, Goo teaches only a single heavily doped area actually within the first doped region, as is required to create a prior art semiconductor memory, the second heavily doped area (as can be seen from Fig.4 of the cited art) being elsewhere on the substrate. The arrangement taught by Goo and consequently a device formed according to Goo's teachings may only provide a single drain signal and therefore can only store a single data bit. The teachings of Goo cannot realize the present invention capability of storing multiple data bits.

The Applicant therefore asserts that claim 1 of the present invention is not anticipated by Goo, reconsideration of claim 1 is politely requested in light of the above discussion.

Claims 2-5, being dependent upon claim 1, should be allowed if claim 1 is found to be allowable.

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Regarding claims 6-11, all limitations of claim 12 are hereby included in the base claim, claim 6, as suggested and claim 12 is hereby cancelled. Since claim 12 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims, allowance of the amended claim 6 is hereby requested. The amended claim 7 and claims 8-11, being dependent upon the amended claim 6 and should be allowable if the amended claim 6 is allowed. Allowance of the amended claim 7 and claims 8-11 is politely requested.

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Sincerely,

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